Jinfei Wu

List of Publications by Year in Descending Order

339 papers	30,355 citations	78 h-index	170 g-index
358 ext. papers	34,033 ext. citations	7.5 avg, IF	6.98 L-index

#	Paper	IF	Citations
339	Performance of the ATLAS Level-1 topological trigger in Run´2. *European Physical Journal C*, **2022**, 82, 1	4.2	0
338	Transducerless time domain reflectance measurement of semiconductor thermal properties. *Journal of Applied Physics*, **2022**, 131, 025101	2.5	0
337	Search for exotic decays of the Higgs boson into b$$ overline{b} $$ and missing transverse momentum in pp collisions at $$ sqrt{s} $$ = 13 TeV with the ATLAS detector. *Journal of High Energy Physics*, **2022**, 2022, 1	5.4	0
336	Observation of electroweak production of two jets in association with an isolated photon and missing transverse momentum, and search for a Higgs boson decaying into invisible particles at 13´$$text {TeV}$$ with the ATLAS detector. *European Physical Journal C*, **2022**, 82, 1	4.2	0
335	Giant Isotope Effect of Thermal Conductivity in Silicon Nanowires.. *Physical Review Letters*, **2022**, 128, 085901	7.4	1
334	Search for Higgs bosons decaying into new spin-0 or spin-1 particles in four-lepton final states with the ATLAS detector with 139 fb1 of pp collision data at $$ sqrt{s} $$ = 13 TeV. *Journal of High Energy Physics*, **2022**, 2022, 1	5.4	0
333	AtlFast3: The Next Generation of Fast Simulation in ATLAS. *Computing and Software for Big Science*, **2022**, 6, 1	6	0
332	Measurement of the energy response of the ATLAS´calorimeter to charged´pions from $$W^{pm }rightarrow tau ^{pm }(rightarrow pi ^{pm }nu _{tau })nu _{tau }$$ events in Run´2 data. *European Physical Journal C*, **2022**, 82, 1	4.2	0
331	Determination of the parton distribution functions of the proton using diverse ATLAS data from pp collisions at $$sqrt{s} = 7$$, 8 and 13 ˆTeV. *European Physical Journal C*, **2022**, 82, 1	4.2	1
330	Temperature-adaptive radiative coating for all-season household thermal regulation.. *Science*, **2021**, 374, 1504-1509	33.3	43
329	Search for R-parity-violating supersymmetry in a final state containing leptons and many jets with the ATLAS experiment using (sqrt{s} = 13hbox { TeV}) proton–proton collision data. *European Physical Journal C*, **2021**, 81, 1	4.2	2
328	Measurement of the t(overline{t})t(overline{t}) production cross section in pp collisions at (sqrt{s}) = 13 TeV with the ATLAS detector. *Journal of High Energy Physics*, **2021**, 2021, 1	5.4	0
327	Tuning of Optical Phonons in -MoO-VO Multilayers. *ACS Applied Materials & Interfaces*, **2021**, 13, 48981-48987	9.5	4
326	Search for dark matter in events with missing transverse momentum and a Higgs boson decaying into two photons in pp collisions at (sqrt{s}) = 13 TeV with the ATLAS detector. *Journal of High Energy Physics*, **2021**, 2021, 1	5.4	2
325	Selective Gas Permeation in Defect-Engineered Bilayer Graphene. *Nano Letters*, **2021**, 21, 2183-2190	11.5	8
324	Thermal camouflaging metamaterials. *Materials Today*, **2021**, 45, 120-141	21.8	48
323	Flat Bands in Magic-Angle Bilayer Photonic Crystals at Small Twists. *Physical Review Letters*, **2021**, 126, 223601	7.4	12

322	Measurements of W+W□ □1 jet production cross-sections in pp collisions at (sqrt{s}) = 13 TeV with the ATLAS detector. *Journal of High Energy Physics*, **2021**, 2021, 1	5.4	0
321	A search for the decays of stopped long-lived particles at (sqrt{mathrm{s}}) = 13 TeV with the ATLAS detector. *Journal of High Energy Physics*, **2021**, 2021, 1	5.4	1
320	Phase change materials in photonic devices. *Journal of Applied Physics*, **2021**, 129, 030902	2.5	13
319	The asymmetry of antimatter in the proton. *Nature*, **2021**, 590, 561-565	50.4	13
318	Search for dark matter produced in association with a Standard Model Higgs boson decaying into b-quarks using the full Run 2 dataset from the ATLAS detector. *Journal of High Energy Physics*, **2021**, 2021, 1	5.4	0
317	Measurement of the production cross section of pairs of isolated photons in pp collisions at 13 TeV with the ATLAS detector. *Journal of High Energy Physics*, **2021**, 2021, 1	5.4	0
316	Search for exotic decays of the Higgs boson into long-lived particles in pp collisions at $$ sqrt{s} $$ = 13 TeV using displaced vertices in the ATLAS inner detector. *Journal of High Energy Physics*, **2021**, 2021, 1	5.4	0
315	Search for charginoneutralino pair production in final states with three leptons and missing transverse momentum in $$sqrt{s} = 13$$ TeV pp collisions with the ATLAS detector. *European Physical Journal C*, **2021**, 81, 1	4.2	1
314	Measurement of b-quark fragmentation properties in jets using the decay B– ->J/K– in pp collisions at $$ sqrt{s} $$ = 13 TeV with the ATLAS detector. *Journal of High Energy Physics*, **2021**, 2021, 1	5.4	0
313	Band Engineering of Large-Twist-Angle Graphene/h-BN Moir Superlattices with Pressure. *Physical Review Letters*, **2020**, 125, 226403	7.4	8
312	Millikelvin-resolved ambient thermography. *Science Advances*, **2020**, 6,	14.3	13
311	Synthesis of Atomically Thin Hexagonal Diamond with Compression. *Nano Letters*, **2020**, 20, 5916-5921	11.5	21
310	Extreme In-Plane Thermal Conductivity Anisotropy in Titanium Trisulfide Caused by Heat-Carrying Optical Phonons. *Nano Letters*, **2020**, 20, 5221-5227	11.5	8
309	Anomalously Suppressed Thermal Conduction by Electron-Phonon Coupling in Charge-Density-Wave Tantalum Disulfide. *Advanced Science*, **2020**, 7, 1902071	13.6	10
308	Effect of heating/cooling dynamics in the hysteresis loop and tunable IR emissivity of VO thin films. *Optics Express*, **2020**, 28, 39203-39215	3.3	4
307	Electric-field control of spin dynamics during magnetic phase transitions. *Science Advances*, **2020**, 6,	14.3	10
306	Disorder recovers the Wiedemann-Franz law in the metallic phase of VO2. *Physical Review B*, **2020**, 102,	3.3	5
305	Adaptive tuning of infrared emission using VO thin films. *Scientific Reports*, **2020**, 10, 11544	4.9	13

304	Nanoscale-femtosecond dielectric response of Mott insulators captured by two-color near-field ultrafast electron microscopy. *Nature Communications*, **2020**, 11, 5770	17.4	13
303	Tunable analog thermal material. *Nature Communications*, **2020**, 11, 6028	17.4	22
302	A Thermal Radiation Modulation Platform by Emissivity Engineering with Graded Metal-Insulator Transition. *Advanced Materials*, **2020**, 32, e1907071	24	27
301	Temperature-dependent growth of hexagonal and monoclinic gallium sulfide films by pulsed-laser deposition. *AIP Advances*, **2020**, 10, 105215	1.5	2
300	Chemical trends of deep levels in van der Waals semiconductors. *Nature Communications*, **2020**, 11, 5373	17.4	3
299	Reducing adhesion energy of nano-electro-mechanical relay contacts by self-assembled Perfluoro (2,3-Dimethylbutan-2-ol) coating. *AIP Advances*, **2019**, 9, 055329	1.5	4
298	Metallo-Hydrogel-Assisted Synthesis and Direct Writing of Transition Metal Dichalcogenides. *Advanced Functional Materials*, **2019**, 29, 1807612	15.6	7
297	Anomalously high electronic thermal conductivity and Lorenz ratio in Bi2Te3 nanoribbons far from the bipolar condition. *Applied Physics Letters*, **2019**, 114, 152101	3.4	3
296	Large bandgap of pressurized trilayer graphene. *Proceedings of the National Academy of Sciences of the United States of America*, **2019**, 116, 9186-9190	11.5	32
295	Ion Write Microthermotics: Programing Thermal Metamaterials at the Microscale. *Nano Letters*, **2019**, 19, 3830-3837	11.5	24
294	Nanoscale Friction on Confined Water Layers Intercalated between MoS2 Flakes and Silica. *Journal of Physical Chemistry C*, **2019**, 123, 8827-8835	3.8	19
293	Thermally Tuning Infrared Light Scattering Using Planar Layered Thin Films and Space Gradient Metasurface. *IEEE Journal of Selected Topics in Quantum Electronics*, **2019**, 25, 1-7	3.8	8
292	FE8 type laboratory testing of white etching crack (WEC) bearing failure mode in 100Cr6. *Wear*, **2019**, 434-435, 202962	3.5	7
291	Watching Dynamic Self-Assembly of Web Buckles in Strained MoS Thin Films. *ACS Nano*, **2019**, 13, 3106-3116	16.6	17
290	Pressure-induced semiconductor-to-metal phase transition of a charge-ordered indium halide perovskite. *Proceedings of the National Academy of Sciences of the United States of America*, **2019**, 116, 23404-23409	11.5	25
289	A 0.2 V Micro-Electromechanical Switch Enabled by a Phase Transition. *Small*, **2018**, 14, e1703621	11	15
288	Recent progresses on physics and applications of vanadium dioxide. *Materials Today*, **2018**, 21, 875-896	21.8	187
287	Two-Dimensional Materials for Thermal Management Applications. *Joule*, **2018**, 2, 442-463	27.8	190

286	Multifunctional Microelectro-Opto-mechanical Platform Based on Phase-Transition Materials. *Nano Letters*, **2018**, 18, 1637-1643	11.5	16
285	Reconfigurable Photonic Platforms: A Lithography-Free and Field-Programmable Photonic Metacanvas (Adv. Mater. 5/2018). *Advanced Materials*, **2018**, 30, 1870034	24	3
284	Substrate modified thermal stability of mono- and few-layer MoS. *Nanoscale*, **2018**, 10, 3540-3546	7.7	32
283	Reconfiguring crystal and electronic structures of MoS by substitutional doping. *Nature Communications*, **2018**, 9, 199	17.4	85
282	Variability Study for Low-Voltage Microelectromechanical Relay Operation. *IEEE Transactions on Electron Devices*, **2018**, 65, 1529-1534	2.9	6
281	On the rational limit cycles of Abel equations. *Chaos, Solitons and Fractals*, **2018**, 110, 28-32	9.3	9
280	Dynamic infrared thin-film absorbers with tunable absorption level based on VO2 phase transition. *Optical Materials Express*, **2018**, 8, 2151	2.6	18
279	Tuning the optical and electrical properties of MoS2 by selective Ag photo-reduction. *Applied Physics Letters*, **2018**, 113, 013105	3.4	9
278	Compensated thermal conductivity of metallically conductive Ta-doped TiO2. *Applied Physics Letters*, **2018**, 113, 022103	3.4	4
277	Black Arsenic: A Layered Semiconductor with Extreme In-Plane Anisotropy. *Advanced Materials*, **2018**, 30, e1800754	24	109
276	A Lithography-Free and Field-Programmable Photonic Metacanvas. *Advanced Materials*, **2018**, 30, 1703878	24	60
275	Selective nitrogen doping of graphene oxide by laser irradiation for enhanced hydrogen evolution activity. *Chemical Communications*, **2018**, 54, 13726-13729	5.8	16
274	Perspectives on Thermoelectricity in Layered and 2D Materials. *Advanced Electronic Materials*, **2018**, 4, 1800248	6.4	47
273	Anomalous Above-Gap Photoexcitations and Optical Signatures of Localized Charge Puddles in Monolayer Molybdenum Disulfide. *ACS Nano*, **2017**, 11, 2115-2123	16.7	25
272	Anomalously low electronic thermal conductivity in metallic vanadium dioxide. *Science*, **2017**, 355, 371-374	33.3	208
271	Pressure-Temperature Phase Diagram of Vanadium Dioxide. *Nano Letters*, **2017**, 17, 2512-2516	11.5	43
270	Search for ferromagnetic order in overdoped copper-oxide superconductors. *Scientific Reports*, **2017**, 7, 45896	4.9	7
269	Pressurizing Field-Effect Transistors of Few-Layer MoS in a Diamond Anvil Cell. *Nano Letters*, **2017**, 17, 194-199	11.5	25

268	Variable range hopping electric and thermoelectric transport in anisotropic black phosphorus. *Applied Physics Letters*, **2017**, 111, 102101	3.4	28
267	Enhancing Modulation of Thermal Conduction in Vanadium Dioxide Thin Film by Nanostructured Nanogaps. *Scientific Reports*, **2017**, 7, 7131	4.9	11
266	Hidden Magnetic States Emergent Under Electric Field, In A Room Temperature Composite Magnetoelectric Multiferroic. *Scientific Reports*, **2017**, 7, 15460	4.9	20
265	Thermal diodes, regulators, and switches: Physical mechanisms and potential applications. *Applied Physics Reviews*, **2017**, 4, 041304	17.3	193
264	Reducing adhesion energy of micro-relay electrodes by ion beam synthesized oxide nanolayers. *APL Materials*, **2017**, 5, 036103	5.7	1
263	Apparent breakdown of Raman selection rule at valley exciton resonances in monolayer MoS2. *Physical Review B*, **2017**, 95,	3.3	26
262	Quantifying van der Waals Interactions in Layered Transition Metal Dichalcogenides from Pressure-Enhanced Valence Band Splitting. *Nano Letters*, **2017**, 17, 4982-4988	11.5	34
261	Interlayer electron□phonon coupling in WSe2/hBN heterostructures. *Nature Physics*, **2017**, 13, 127-131	16.2	129
260	On Optical Dipole Moment and Radiative Recombination Lifetime of Excitons in WSe2. *Advanced Functional Materials*, **2017**, 27, 1601741	15.6	31
259	The Demise of Superfluid Density in Overdoped La2□ Sr x CuO4 Films Grown by Molecular Beam Epitaxy. *Journal of Superconductivity and Novel Magnetism*, **2017**, 30, 1345-1348	1.5	2
258	Mechanical properties of two-dimensional materials and heterostructures. *Journal of Materials Research*, **2016**, 31, 832-844	2.5	53
257	Bimodal Control of Heat Transport at Graphene-Metal Interfaces Using Disorder in Graphene. *Scientific Reports*, **2016**, 6, 34428	4.9	5
256	Perspective: Rapid synthesis of complex oxides by combinatorial molecular beam epitaxy. *APL Materials*, **2016**, 4, 053205	5.7	8
255	Ferroelectrically Gated Atomically Thin Transition-Metal Dichalcogenides as Nonvolatile Memory. *Advanced Materials*, **2016**, 28, 2923-30	24	103
254	Bandgap Restructuring of the Layered Semiconductor Gallium Telluride in Air. *Advanced Materials*, **2016**, 28, 6465-70	24	42
253	Characterization of structural change in rail surface using advanced automatic crystallographic orientation microscopy **2016**,		2
252	Reconstruction of the Nanoscale Three-Dimensional Mass-Density Autocorrelation Function of Individual Cells. *Microscopy and Microanalysis*, **2016**, 22, 918-919	0.5	
251	Crossing Thermal Lubricity and Electronic Effects in Friction: Vanadium Dioxide under the Metal□nsulator Transition. *Advanced Materials Interfaces*, **2016**, 3, 1500388	4.6	9

250	Modulating Photoluminescence of Monolayer Molybdenum Disulfide by Metal-Insulator Phase Transition in Active Substrates. *Small*, **2016**, 12, 3976-84	11	24
249	Site Selective Doping of Ultrathin Metal Dichalcogenides by Laser-Assisted Reaction. *Advanced Materials*, **2016**, 28, 341-6	24	75
248	Pressure-induced structural transition of CdxZn1□O alloys. *Applied Physics Letters*, **2016**, 108, 152105	3.4	9
247	Stress compensation for arbitrary curvature control in vanadium dioxide phase transition actuators. *Applied Physics Letters*, **2016**, 109, 023504	3.4	14
246	Sub-50 mV NEM relay operation enabled by self-assembled molecular coating **2016**,		18
245	Laser-Assisted Doping: Site Selective Doping of Ultrathin Metal Dichalcogenides by Laser-Assisted Reaction (Adv. Mater. 2/2016). *Advanced Materials*, **2016**, 28, 392-392	24	1
244	Multilayer ReS2lateral p□ homojunction for photoemission and photodetection. *Applied Physics Express*, **2016**, 9, 055201	2.4	17
243	Nanotexturing To Enhance Photoluminescent Response of Atomically Thin Indium Selenide with Highly Tunable Band Gap. *Nano Letters*, **2016**, 16, 3221-9	11.5	119
242	Stability Studies of MAPbI 3 : Identification of Degradation Pathways and Strategies for Observing the Native Structure of Lead Halide Perovskites. *Microscopy and Microanalysis*, **2016**, 22, 1510-1511	0.5	0
241	MoS2 Heterojunctions by Thickness Modulation. *Scientific Reports*, **2015**, 5, 10990	4.9	71
240	Thermal tuning of infrared resonant absorbers based on hybrid gold-VO2 nanostructures. *Applied Physics Letters*, **2015**, 106, 161104	3.4	115
239	3D LITHOGRAPHY. Atomic gold-enabled three-dimensional lithography for silicon mesostructures. *Science*, **2015**, 348, 1451-5	33.3	73
238	Pressure-induced phase transitions and metallization in VO2. *Physical Review B*, **2015**, 91,	3.3	63
237	Visualizing nanoscale excitonic relaxation properties of disordered edges and grain boundaries in monolayer molybdenum disulfide. *Nature Communications*, **2015**, 6, 7993	17.4	172
236	Anisotropic in-plane thermal conductivity of black phosphorus nanoribbons at temperatures higher than 100 K. *Nature Communications*, **2015**, 6, 8573	17.4	249
235	Electronic structure, spin-orbit coupling, and interlayer interaction in bulk MoS2 and WS2. *Physical Review B*, **2015**, 91,	3.3	92
234	Vibrational spectrum renormalization by enforced coupling across the van der Waals gap between MoS2 and WS2 monolayers. *Physical Review B*, **2015**, 92,	3.3	19
233	Intensity tunable infrared broadband absorbers based on VO2 phase transition using planar layered thin films. *Scientific Reports*, **2015**, 5, 13384	4.9	71

232	Hopping conduction in p-type MoS2 near the critical regime of the metal-insulator transition. *Applied Physics Letters*, **2015**, 107, 223107	3.4	17
231	Self-Passivation of Defects: Effects of High-Energy Particle Irradiation on the Elastic Modulus of Multilayer Graphene. *Advanced Materials*, **2015**, 27, 6841-7	24	21
230	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi□Te□by Multifunctionality of Native Defects. *Advanced Materials*, **2015**, 27, 3681-6	24	79
229	Directly Metering Light Absorption and Heat Transfer in Single Nanowires Using Metal□nsulator Transition in VO2. *Advanced Optical Materials*, **2015**, 3, 336-341	8.1	20
228	Perspective: Extremely fine tuning of doping enabled by combinatorial molecular-beam epitaxy. *APL Materials*, **2015**, 3, 062401	5.7	14
227	Study on the fabrication and performance of Mn1.56Co0.96Ni0.48O4 film optically immersed infrared detector. *Materials Research Innovations*, **2015**, 19, S7-S10	1.9	6
226	Large resistivity modulation in mixed-phase metallic systems. *Nature Communications*, **2015**, 6, 5959	17.4	132
225	Fermi-level stabilization in the topological insulators Bi2Se3 and Bi2Te3: Origin of the surface electron gas. *Physical Review B*, **2014**, 89,	3.3	39
224	Tuning interlayer coupling in large-area heterostructures with CVD-grown MoS2 and WS2 monolayers. *Nano Letters*, **2014**, 14, 3185-90	11.5	562
223	Scalable enhancement of graphene oxide properties by thermally driven phase transformation. *Nature Chemistry*, **2014**, 6, 151-8	17.6	261
222	Monolayer behaviour in bulk ReS2 due to electronic and vibrational decoupling. *Nature Communications*, **2014**, 5, 3252	17.4	728
221	Two-dimensional semiconductor alloys: Monolayer Mo1□WxSe2. *Applied Physics Letters*, **2014**, 104, 012101	3.4	122
220	Direct observation of nanoscale Peltier and Joule effects at metal-insulator domain walls in vanadium dioxide nanobeams. *Nano Letters*, **2014**, 14, 2394-400	11.5	27
219	Probing local strain at MX(2)-metal boundaries with surface plasmon-enhanced Raman scattering. *Nano Letters*, **2014**, 14, 5329-34	11.5	87
218	Elastic properties of chemical-vapor-deposited monolayer MoS2, WS2, and their bilayer heterostructures. *Nano Letters*, **2014**, 14, 5097-103	11.5	384
217	Gate-dependent pseudospin mixing in graphene/boron nitride moir□superlattices. *Nature Physics*, **2014**, 10, 743-747	16.2	53
216	Ultrafast charge transfer in atomically thin MoS□WS□heterostructures. *Nature Nanotechnology*, **2014**, 9, 682-6	28.7	1432
215	Temperature-gated thermal rectifier for active heat flow control. *Nano Letters*, **2014**, 14, 4867-72	11.5	104

214	Structural and electrical properties of Mn1.56Co0.96Ni0.48O4 NTC thermistor films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2014**, 185, 74-78	3.1	23
213	Powerful, multifunctional torsional micromuscles activated by phase transition. *Advanced Materials*, **2014**, 26, 1746-50	24	65
212	Versatile cold atom source for multi-species experiments. *Review of Scientific Instruments*, **2014**, 85, 113103	1.3	4
211	Vanadium dioxide nanowire-based microthermometer for quantitative evaluation of electron beam heating. *Nature Communications*, **2014**, 5, 4986	17.4	39
210	Doping against the native propensity of MoS2: degenerate hole doping by cation substitution. *Nano Letters*, **2014**, 14, 6976-82	11.5	468
209	Formation and stability of point defects in monolayer rhenium disulfide. *Physical Review B*, **2014**, 89,	3.3	118
208	Infrared optical properties of Mn1.56Co0.96Ni0.48O4 thin films prepared by chemical solution deposition. *Applied Physics A: Materials Science and Processing*, **2014**, 114, 829-832	2.6	13
207	Anomalous independence of interface superconductivity from carrier density. *Nature Materials*, **2013**, 12, 877-81	27	77
206	Dynamically tracking the strain across the metal-insulator transition in VO2 measured using electromechanical resonators. *Nano Letters*, **2013**, 13, 4685-9	11.5	13
205	Monolayer semiconducting transition metal dichalcogenide alloys: Stability and band bowing. *Journal of Applied Physics*, **2013**, 113, 143703	2.5	175
204	Defects activated photoluminescence in two-dimensional semiconductors: interplay between bound, charged, and free excitons. *Scientific Reports*, **2013**, 3, 2657	4.9	726
203	Mechanically modulated tunneling resistance in monolayer MoS2. *Applied Physics Letters*, **2013**, 103, 183105	3.4	36
202	Work function engineering of single layer graphene by irradiation-induced defects. *Applied Physics Letters*, **2013**, 103, 171604	3.4	92
201	Band offsets and heterostructures of two-dimensional semiconductors. *Applied Physics Letters*, **2013**, 102, 012111	3.4	1131
200	Stable p- and n-type doping of few-layer graphene/graphite. *Carbon*, **2013**, 57, 507-514	10.4	32
199	Axially engineered metal-insulator phase transition by graded doping VO2 nanowires. *Journal of the American Chemical Society*, **2013**, 135, 4850-5	16.4	84
198	Phase transformation and thermoelectric properties of bismuth-telluride nanowires. *Nanoscale*, **2013**, 5, 4669-72	7.7	54
197	Anomalous Raman spectra and thickness-dependent electronic properties of WSe2. *Physical Review B*, **2013**, 87,	3.3	341

196	Broad-range modulation of light emission in two-dimensional semiconductors by molecular physisorption gating. *Nano Letters*, **2013**, 13, 2831-6	11.5	566
195	Comprehensive study of the metal-insulator transition in pulsed laser deposited epitaxial VO2 thin films. *Journal of Applied Physics*, **2013**, 113, 043707	2.5	105
194	Performance limits of microactuation with vanadium dioxide as a solid engine. *ACS Nano*, **2013**, 7, 2266-72	12.7	55
193	Microstructure of Mg doped GaNAs alloys. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 453-456		1
192	Metal to semiconductor transition in metallic transition metal dichalcogenides. *Journal of Applied Physics*, **2013**, 114, 174307	2.5	24
191	Suppression of thermal conductivity in InxGa1−xN alloys by nanometer-scale disorder. *Applied Physics Letters*, **2013**, 102, 121906	3.4	42
190	Local structure of amorphous GaN1−xAsx semiconductor alloys across the composition range. *Journal of Applied Physics*, **2013**, 113, 243505	2.5	6
189	Nanomechanical actuation from phase transitions in individual VO2 micro-beams. *Applied Physics Letters*, **2013**, 102, 231909	3.4	16
188	Enhancing structural transition by carrier and quantum confinement: Stabilization of cubic InN quantum dots by Mn incorporation. *Applied Physics Letters*, **2013**, 103, 253102	3.4	3
187	Environmentally stable/self-powered ultraviolet photodetectors with high sensitivity. *Applied Physics Letters*, **2013**, 103, 143503	3.4	20
186	Strain and temperature dependence of the insulating phases of VO2 near the metal-insulator transition. *Physical Review B*, **2012**, 85,	3.3	156
185	New Opportunities on Phase Transitions of Correlated Electron Nanostructures. *Springer Series in Materials Science*, **2012**, 3-22	0.9	1
184	Giant-amplitude, high-work density microactuators with phase transition activated nanolayer bimorphs. *Nano Letters*, **2012**, 12, 6302-8	11.5	124
183	Dense electron system from gate-controlled surface metal-insulator transition. *Nano Letters*, **2012**, 12, 6272-7	11.5	48
182	Bandgap engineering in MBE grown Al1−xGaxN epitaxial columnar nanostructures. *Journal Physics D: Applied Physics*, **2012**, 45, 015104	3	4
181	Thermally driven crossover from indirect toward direct bandgap in 2D semiconductors: MoSe2 versus MoS2. *Nano Letters*, **2012**, 12, 5576-80	11.5	989
180	Molecular beam epitaxy of GaN1−xBix alloys with high bismuth content. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 419-423	1.6	10
179	Magnetic properties of MoS2: Existence of ferromagnetism. *Applied Physics Letters*, **2012**, 101, 123105	3.4	218

178	Ultra-long, free-standing, single-crystalline vanadium dioxide micro/nanowires grown by simple thermal evaporation. *Applied Physics Letters*, **2012**, 100, 103111	3.4	93
177	Unusually long free carrier lifetime and metal-insulator band offset in vanadium dioxide. *Physical Review B*, **2012**, 85,	3.3	36
176	Decoupling of structural and electronic phase transitions in VO2. *Physical Review Letters*, **2012**, 109, 166406	7.4	131
175	Large reaction rate enhancement in formation of ultrathin AuSi eutectic layers. *Physical Review Letters*, **2012**, 108, 096102	7.4	11
174	Directed assembly of nano-scale phase variants in highly strained BiFeO3 thin films. *Journal of Applied Physics*, **2012**, 112, 064102	2.5	32
173	Visualizing Native Cell Nano-architecture During Early Carcinogenesis Using Scanning Transmission Electron Microscopy. *Microscopy and Microanalysis*, **2012**, 18, 1642-1643	0.5	1
172	Efficient photovoltaic current generation at ferroelectric domain walls. *Physical Review Letters*, **2011**, 107, 126805	7.4	309
171	Mechanics and dynamics of the strain-induced M1-M2 structural phase transition in individual VO nanowires. *Nano Letters*, **2011**, 11, 3207-13	11.5	173
170	Thermal stability of amorphous GaN1Asx alloys. *Applied Physics Letters*, **2011**, 98, 161902	3.4	7
169	Epidermal electronics. *Science*, **2011**, 333, 838-43	33.3	3216
168	Intrinsic optical properties of vanadium dioxide near the insulator-metal transition. *Nano Letters*, **2011**, 11, 466-70	11.5	72
167	Large kinetic asymmetry in the metal-insulator transition nucleated at localized and extended defects. *Physical Review B*, **2011**, 83,	3.3	78
166	Direct observation of imprinted antiferromagnetic vortex states in CoO/Fe/Ag(001) discs. *Nature Physics*, **2011**, 7, 303-306	16.2	66
165	Thickness and mosaic morphology of InAs films grown by LPE supercooling technique. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 811-814	2.1	1
164	GaNAs alloys over the whole composition range grown on crystalline and amorphous substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2503-2505		7
163	Field-effect modulation of conductance in VO2 nanobeam transistors with HfO2 as the gate dielectric. *Applied Physics Letters*, **2011**, 99, 062114	3.4	67
162	Electrothermal dynamics of semiconductor nanowires under local carrier modulation. *Nano Letters*, **2011**, 11, 3809-15	11.5	45
161	Heat transfer across the interface between nanoscale solids and gas. *ACS Nano*, **2011**, 5, 10102-7	16.7	55

160	Strain effects in low-dimensional transition metal oxides. *Materials Science and Engineering Reports*, **2011**, 71, 35-52	30.9	115
159	Continuous spin reorientation transition in epitaxial antiferromagnetic NiO thin films. *Physical Review B*, **2011**, 84,	3.3	16
158	Electrothermally driven current vortices in inhomogeneous bipolar semiconductors. *Physical Review B*, **2011**, 84,	3.3	16
157	Construction of the Magnetic Phase Diagram of FeMn/Ni/Cu(001) Using Photoemission Electron Microscopy. *IEEE Transactions on Magnetics*, **2011**, 47, 1631-1634	2	1
156	Determination of spin-polarized quantum well states and spin-split energy dispersions of Co ultrathin films grown on Mo(110). *Physical Review B*, **2011**, 83,	3.3	10
155	Mismatched alloy nanowires for electronic structure tuning. *Applied Physics Letters*, **2011**, 99, 233111	3.4	2
154	Decoupling single nanowire mobilities limited by surface scattering and bulk impurity scattering. *Journal of Applied Physics*, **2011**, 110, 033705	2.5	11
153	Element-specific study of epitaxial NiO/Ag/CoO/Fe films grown on vicinal Ag(001) using photoemission electron microscopy. *Applied Physics Letters*, **2011**, 98, 212508	3.4	9
152	An analytical model of strain isolation for stretchable and flexible electronics. *Applied Physics Letters*, **2011**, 98, 061902	3.4	38
151	Doping of GaN1−xAsx with high As content. *Journal of Applied Physics*, **2011**, 110, 093702	2.5	4
150	Effects of point defects on thermal and thermoelectric properties of InN. *Applied Physics Letters*, **2011**, 98, 012108	3.4	36
149	Growth and transport properties of p-type GaNBi alloys. *Journal of Materials Research*, **2011**, 26, 2887-2894	2.5	15
148	Determination of the minority carrier diffusion length in compositionally graded Cu(In,Ga)Se2 solar cells using electron beam induced current. *Applied Physics Letters*, **2010**, 96, 022104	3.4	52
147	GaN1−xBix: Extremely mismatched semiconductor alloys. *Applied Physics Letters*, **2010**, 97, 141919	3.4	31
146	Microstructured elastomeric surfaces with reversible adhesion and examples of their use in deterministic assembly by transfer printing. *Proceedings of the National Academy of Sciences of the United States of America*, **2010**, 107, 17095-100	11.5	280
145	Thermodynamics of strained vanadium dioxide single crystals. *Journal of Applied Physics*, **2010**, 108, 083517	2.5	57
144	Four-fold magnetic anisotropy induced by the antiferromagnetic order in FeMn/Co/Cu(001) system. *Journal of Applied Physics*, **2010**, 108, 073905	2.5	25
143	Evolution of microstructure and related properties of PbZr0.4Ti0.6O3 films on F-doped tin oxide with annealing temperature. *Journal of Applied Physics*, **2010**, 107, 084103	2.5	6

142	Rotatable magnetic anisotropy of CoO/Fe/Ag(001) in ultrathin regime of the CoO layer. *Applied Physics Letters*, **2010**, 97, 042505	3.4	12
141	Effect of NiO spin orientation on the magnetic anisotropy of the Fe film in epitaxially grown Fe/NiO/Ag(001) and Fe/NiO/MgO(001). *Physical Review B*, **2010**, 81,	3.3	27
140	Low gap amorphous GaN1−xAsx alloys grown on glass substrate. *Applied Physics Letters*, **2010**, 97, 101906	3.4	16
139	Extended mapping and exploration of the vanadium dioxide stress-temperature phase diagram. *Nano Letters*, **2010**, 10, 2667-73	11.5	186
138	Enhancing the thermoelectric power factor with highly mismatched isoelectronic doping. *Physical Review Letters*, **2010**, 104, 016602	7.4	87
137	Direct measurement of rotatable and frozen CoO spins in exchange bias system of CoO/Fe/Ag(001). *Physical Review Letters*, **2010**, 104, 217204	7.4	97
136	Constant threshold resistivity in the metal-insulator transition of VO2. *Physical Review B*, **2010**, 82,	3.3	40
135	Colossal thermal-mechanical actuation via phase transition in single-crystal VO2 microcantilevers. *Journal of Applied Physics*, **2010**, 108, 083538	2.5	67
134	Temperature dependent optical properties of Mn doped (Pb,Sr)TiO3 ferroelectric films in absorption region: Electron–phonon interaction. *Journal of Applied Physics*, **2010**, 108, 114102	2.5	16
133	Switching a magnetic vortex by interlayer coupling in epitaxially grown Co/Cu/Py/Cu(001) trilayer disks. *Journal of Physics Condensed Matter*, **2010**, 22, 342001	1.8	8
132	Effects of substrate temperature on the dielectric function of ZnO films. *Applied Physics A: Materials Science and Processing*, **2010**, 98, 129-134	2.6	10
131	Finite element simulations of compositionally graded InGaN solar cells. *Solar Energy Materials and Solar Cells*, **2010**, 94, 478-483	6.4	145
130	Tailoring exchange bias by oxidizing Co film across a Cu wedge in Cu(wedge)/CoO/Co/Cu(0 0 1). *Journal of Magnetism and Magnetic Materials*, **2010**, 322, 2728-2731	2.8	
129	Effect of inserting Ni and Co layers on the quantum well states of a thin Cu film grown on Co/Cu(001). *Physical Review B*, **2009**, 80,	3.3	2
128	Superelastic metal-insulator phase transition in single-crystal VO2 nanobeams. *Physical Review B*, **2009**, 80,	3.3	33
127	Stripe-to-bubble transition of magnetic domains at the spin reorientation of (Fe/Ni)/Cu/Ni/Cu(001). *Physical Review B*, **2009**, 79,	3.3	12
126	Ni spin switching induced by magnetic frustration in FeMn/Ni/Cu(001). *Physical Review B*, **2009**, 79,	3.3	20
125	Numerical simulations of novel InGaN solar cells **2009**,		2

124	Element-specific study of the anomalous magnetic interlayer coupling across NiO spacer layer in Co/NiO/Fe/Ag(001) using XMCD and XMLD. *Physical Review B*, **2009**, 80,	3.3	21
123	Optical properties of Mn1.56Co0.96Ni0.48O4 films studied by spectroscopic ellipsometry. *Applied Physics Letters*, **2009**, 94, 011106	3.4	34
122	Determining surface Fermi level pinning position of InN nanowires using electrolyte gating. *Applied Physics Letters*, **2009**, 95, 173114	3.4	16
121	Quantum well states in Au/Ru(0001) and their effect on the magnetic properties of a Co overlayer. *New Journal of Physics*, **2009**, 11, 043016	2.9	9
120	Third generation photovoltaics. *Laser and Photonics Reviews*, **2009**, 3, 394-405	8.3	142
119	Synthesis and Ex situ doping of ZnTe and ZnSe nanostructures with extreme aspect ratios. *Nano Research*, **2009**, 2, 931-937	10	13
118	Structural perfection of InGaN layers and its relation to photoluminescence. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 2626-2631		13
117	Strain engineering and one-dimensional organization of metal-insulator domains in single-crystal vanadium dioxide beams. *Nature Nanotechnology*, **2009**, 4, 732-7	28.7	480
116	Dopant profiling and surface analysis of silicon nanowires using capacitance-voltage measurements. *Nature Nanotechnology*, **2009**, 4, 311-4	28.7	145
115	When group-III nitrides go infrared: New properties and perspectives. *Journal of Applied Physics*, **2009**, 106, 011101	2.5	661
114	Printed assemblies of inorganic light-emitting diodes for deformable and semitransparent displays. *Science*, **2009**, 325, 977-81	33.3	617
113	Sublimation of GeTe nanowires and evidence of its size effect studied by in situ TEM. *Journal of the American Chemical Society*, **2009**, 131, 14526-30	16.4	30
112	Thermoelectric effect across the metal-insulator domain walls in VO2 microbeams. *Nano Letters*, **2009**, 9, 4001-6	11.5	71
111	Optical Properties of InN and Related Alloys **2009**, 243-272		
110	An excess of cosmic ray electrons at energies of 300-800 GeV. *Nature*, **2008**, 456, 362-5	50.4	791
109	Electronic Band Structure of Highly Mismatched Semiconductor Alloys **2008**, 65-89		3
108	Retrieving the energy band of Cu thin films using quantum well states. *Journal of Physics Condensed Matter*, **2008**, 20, 035213	1.8	2
107	Probing and modulating surface electron accumulation in InN by the electrolyte gated Hall effect. *Applied Physics Letters*, **2008**, 93, 262105	3.4	29

106	Epitaxial semiconductor quantum wires. *Journal of Nanoscience and Nanotechnology*, **2008**, 8, 3300-14	1.3	2
105	Mg-doped InN and InGaN Photoluminescence, capacitance oltage and thermopower measurements. *Physica Status Solidi (B): Basic Research*, **2008**, 245, 873-877	1.3	53
104	Energetic Beam Synthesis of Dilute Nitrides and Related Alloys **2008**, 1-34		
103	Current-driven phase oscillation and domain-wall propagation in WxV1-xO2 nanobeams. *Nano Letters*, **2007**, 7, 363-6	11.5	118
102	Effects of quantum confinement on the doping limit of semiconductor nanowires. *Nano Letters*, **2007**, 7, 1186-90	11.5	59
101	Valence band anticrossing in mismatched III-V semiconductor alloys. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 1711-1714		2
100	Gate coupling and charge distribution in nanowire field effect transistors. *Nano Letters*, **2007**, 7, 2778-83	11.5	106
99	Effect of step decoration on the spin reorientation of Ni films grown on vicinal Cu(001). *Physical Review B*, **2007**, 76,	3.3	3
98	Effect of atomic steps on the interfacial interaction of FeMn Co films grown on vicinal Cu(001). *Physical Review B*, **2007**, 76,	3.3	11
97	Symmetry-breaking induced exchange bias in ferromagnetic Ni-Cu-Co and Ni-Fe-Co sandwiches grown on a vicinal Cu(001) surface. *Physical Review Letters*, **2007**, 99, 077203	7.4	10
96	Valence-band anticrossing in mismatched III-V semiconductor alloys. *Physical Review B*, **2007**, 75,	3.3	310
95	Effects of surface states on electrical characteristics of InN and In1 GaxN. *Physical Review B*, **2007**, 76,	3.3	57
94	Magnetic bubble domain phase at the spin reorientation transition of ultrathin Fe/Ni/Cu(001) film. *Physical Review Letters*, **2007**, 98, 207205	7.4	55
93	NEW DEVELOPMENTS IN DILUTE NITRIDE SEMICONDUCTOR RESEARCH **2006**, 399-428		2
92	Strain-induced self organization of metal-insulator domains in single-crystalline VO2 nanobeams. *Nano Letters*, **2006**, 6, 2313-7	11.5	261
91	Structure and electronic properties of InN and In-rich group III-nitride alloys. *Journal Physics D: Applied Physics*, **2006**, 39, R83-R99	3	211
90	Germanium telluride nanowires and nanohelices with memory-switching behavior. *Journal of the American Chemical Society*, **2006**, 128, 8148-9	16.4	117
89	Native defects in InxGa1 N alloys. *Physica B: Condensed Matter*, **2006**, 376-377, 432-435	2.8	8

88	Fermi-level stabilization energy in group III nitrides. *Physical Review B*, **2005**, 71,	3.3	172
87	Magnetic stripe melting at the spin reorientation transition in Fe□Ni□Cu(001). *Physical Review B*, **2005**, 71,	3.3	66
86	Band Anticrossing and Related Electronic Structure in III□N-V Alloys **2005**, 325-359		5
85	Effect of Mn overlayer on spin reorientation transition at Ni/Cu(001). *Journal of Magnetism and Magnetic Materials*, **2005**, 286, 497-500	2.8	3
84	Investigation of microstructure and V-defect formation in InxGa1□N/GaN MQW grown using temperature-gradient metalorganic chemical vapor deposition. *Journal of Electronic Materials*, **2005**, 34, 605-611	1.9	7
83	Effect of native defects on optical properties of InxGa1□N alloys. *Applied Physics Letters*, **2005**, 87, 161905	3.4	18
82	Group III-nitride Materials for High Efficiency Photoelectrochemical Cells. *Materials Research Society Symposia Proceedings*, **2005**, 884, 1		3
81	Electronic and Optical Properties of Energetic Particle-Irradiated In-rich InGaN. *Materials Research Society Symposia Proceedings*, **2005**, 864, 7101		1
80	Highly Mismatched Alloys for Intermediate Band Solar Cells. *Materials Research Society Symposia Proceedings*, **2005**, 865, 571		7
79	Mutual Passivation in Dilute GaNxAs1-x Alloys. *Materials Research Society Symposia Proceedings*, **2005**, 864, 811		
78	High quality InN/GaN heterostructures grown by migration enhanced metalorganic chemical vapor deposition. *Applied Physics Letters*, **2004**, 84, 1892-1894	3.4	52
77	Structure-Dependent Hydrostatic Deformation Potentials of Individual Single-Walled Carbon Nanotubes. *Physical Review Letters*, **2004**, 93,	7.4	46
76	Size self-scaling effect in stacked InAs□InAlAs nanowire multilayers. *Applied Physics Letters*, **2004**, 85, 5061-5063	3.4	2
75	Synthesis and optical properties of II-O-VI highly mismatched alloys. *Journal of Applied Physics*, **2004**, 95, 6232-6238	2.5	55
74	Effect of gallium nitride template layer strain on the growth of InxGa1-xN□GaN multiple quantum well light emitting diodes. *Journal of Applied Physics*, **2004**, 96, 1381-1386	2.5	31
73	Temperature-dependent magnetization in a ferromagnetic bilayer consisting of two materials with different Curie temperatures. *Physical Review B*, **2004**, 70,	3.3	5
72	Effects of pressure on the band structure of highly mismatched Zn1□MnyOxTe1□ alloys. *Applied Physics Letters*, **2004**, 84, 924-926	3.4	10
71	Effects of electron concentration on the optical absorption edge of InN. *Applied Physics Letters*, **2004**, 84, 2805-2807	3.4	210

70	Compositional Ordering in InxGa1-xN and its influence on optical properties. *Materials Research Society Symposia Proceedings*, **2004**, 831, 126		
69	Group III-nitride alloys as photovoltaic materials **2004**,		5
68	Synthesis and properties of highly mismatched II□□VI alloys. *IEE Proceedings: Optoelectronics*, **2004**, 151, 452-459		3
67	Mutual passivation effects in highly mismatched group III□V□N alloys. *IEE Proceedings: Optoelectronics*, **2004**, 151, 460-464		5
66	Growth and characterization of InxGa1□N MQW using a novel method of temperature gradient OMVPE. *Journal of Crystal Growth*, **2004**, 261, 44-49	1.6	7
65	Diluted ZnMnTe oxide: a multi-band semiconductor for high efficiency solar cells. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 660-663	1.3	22
64	Oxygen induced band-gap reduction in ZnOxSe1□ alloys. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 603-606	1.3	6
63	Pressure-dependent photoluminescence study of CuGaSe2. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 3117-3122	1.3	4
62	Effects of hydrostatic pressure on optical properties of InN and In-rich group III-nitride alloys. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 3107-3112	1.3	5
61	Pressure dependence of optical transitions in semiconducting single-walled carbon nanotubes. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 3367-3373	1.3	6
60	Optical properties and electronic structure of InN and In-rich group III-nitride alloys. *Journal of Crystal Growth*, **2004**, 269, 119-127	1.6	145
59	Valence band hybridization in N-rich GaN1□Asx alloys. *Physical Review B*, **2004**, 70,	3.3	76
58	Band anticrossing in dilute nitrides. *Journal of Physics Condensed Matter*, **2004**, 16, S3355-S3372	1.8	26
57	Pressure dependence of the fundamental band-gap energy of CdSe. *Applied Physics Letters*, **2004**, 84, 67-69	3.4	58
56	Raman Spectroscopy and Time-Resolved Photoluminescence of BN and BxCyNz Nanotubes. *Nano Letters*, **2004**, 4, 647-650	11.5	175
55	Synthesis and gas sensitivity of In-doped ZnO nanoparticles. *Journal of Materials Science: Materials in Electronics*, **2003**, 14, 521-526	2.1	50
54	Diluted II-VI oxide semiconductors with multiple band gaps. *Physical Review Letters*, **2003**, 91, 246403	7.4	219
53	Band gaps of InN and group III nitride alloys. *Superlattices and Microstructures*, **2003**, 34, 63-75	2.8	137

52	Mutual passivation of group IV donors and isovalent nitrogen in diluted GaNxAs1− alloys. *Physica B: Condensed Matter*, **2003**, 340-342, 389-393	2.8	3
51	Universal bandgap bowing in group-III nitride alloys. *Solid State Communications*, **2003**, 127, 411-414	1.6	92
50	Narrow bandgap group III-nitride alloys. *Physica Status Solidi (B): Basic Research*, **2003**, 240, 412-416	1.3	20
49	Temperature dependence of the fundamental band gap of InN. *Journal of Applied Physics*, **2003**, 94, 4457-4460	2.5	337
48	Superior radiation resistance of In1−GaxN alloys: Full-solar-spectrum photovoltaic material system. *Journal of Applied Physics*, **2003**, 94, 6477-6482	2.5	503
47	Band-gap bowing effects in BxGa1−As alloys. *Journal of Applied Physics*, **2003**, 93, 2696-2699	2.5	35
46	Effect of oxygen on the electronic band structure in ZnOxSe1− alloys. *Applied Physics Letters*, **2003**, 83, 299-301	3.4	70
45	Composition dependence of the hydrostatic pressure coefficients of the bandgap of ZnSe1−Tex alloys. *Physical Review B*, **2003**, 68,	3.3	16
44	Mutual passivation effects in Si-doped diluted InyGa1−As1−Nx alloys. *Physical Review B*, **2003**, 68,	3.3	14
43	Origin of the large band-gap bowing in highly mismatched semiconductor alloys. *Physical Review B*, **2003**, 67,	3.3	61
42	Mutual passivation of group IV donors and nitrogen in diluted GaNxAs1− alloys. *Applied Physics Letters*, **2003**, 83, 2844-2846	3.4	16
41	Growth of non-polar a-plane and cubic InN on r-plane sapphire by molecular beam epitaxy. *Materials Research Society Symposia Proceedings*, **2003**, 798, 283		
40	Pressure Dependence of Optical Transitions in In-rich Group III-Nitride Alloys. *Materials Research Society Symposia Proceedings*, **2003**, 798, 301		
39	Hydrostatic pressure dependence of the fundamental bandgap of InN and In-rich group III nitride alloys. *Applied Physics Letters*, **2003**, 83, 4963-4965	3.4	63
38	Synthesis of GaNxAs1− thin films by pulsed laser melting and rapid thermal annealing of N+-implanted GaAs. *Journal of Applied Physics*, **2003**, 94, 1043-1049	2.5	43
37	Structural and electronic properties of amorphous and polycrystalline In2Se3 films. *Journal of Applied Physics*, **2003**, 94, 2390-2397	2.5	42
36	Optical properties of single-crystalline ZnO nanowires on m-sapphire. *Applied Physics Letters*, **2003**, 82, 2023-2025	3.4	262
35	Growth of a-plane InN on r-plane sapphire with a GaN buffer by molecular-beam epitaxy. *Applied Physics Letters*, **2003**, 83, 1136-1138	3.4	80

34	Z-Contrast Imaging of InAs Quantum Wires In GaAs/ALAs Quantum Wells. *Microscopy and Microanalysis*, **2002**, 8, 1190-1191	0.5	
33	Preparation and Transport Properties of Li-Doped NiO and (Li + Ca)-Doped NiO Oxides. *Physica Status Solidi A*, **2002**, 193, 78-85		8
32	Band anticrossing in highly mismatched group II-VI semiconductor alloys. *Journal of Electronic Materials*, **2002**, 31, 754-758	1.9	6
31	Mutual passivation of electrically active and isovalent impurities. *Nature Materials*, **2002**, 1, 185-9	27	51
30	Growth of Thick InN by Molecular Beam Epitaxy. *Materials Research Society Symposia Proceedings*, **2002**, 743, L4.10.1		30
29	Band anticrossing in highly mismatched III V semiconductor alloys. *Semiconductor Science and Technology*, **2002**, 17, 860-869	1.8	262
28	Small band gap bowing in In1□GaxN alloys. *Applied Physics Letters*, **2002**, 80, 4741-4743	3.4	498
27	Unusual properties of the fundamental band gap of InN. *Applied Physics Letters*, **2002**, 80, 3967-3969	3.4	1254
26	Band structure of highly mismatched semiconductor alloys: Coherent potential approximation. *Physical Review B*, **2002**, 65,	3.3	61
25	Band anticrossing in GaP1□Nx alloys. *Physical Review B*, **2002**, 65,	3.3	62
24	Si doping of high-Al-mole fraction AlxGa1□N alloys with rf plasma-induced molecular-beam-epitaxy. *Applied Physics Letters*, **2002**, 81, 5192-5194	3.4	29
23	Effects of the narrow band gap on the properties of InN. *Physical Review B*, **2002**, 66,	3.3	346
22	Band anticrossing in group II-Ox VI1□ highly mismatched alloys: Cd1□MnyOxTe1□ quaternaries synthesized by O ion implantation. *Applied Physics Letters*, **2002**, 80, 1571-1573	3.4	30
21	Band anticrossing effects in MgyZn1 Te1□Sex alloys. *Applied Physics Letters*, **2002**, 80, 34-36	3.4	13
20	SYMMETRY IN THE DIAGONAL SELF-ASSEMBLED InAs QUANTUM WIRE ARRAYS ON InP SUBSTRATE. *International Journal of Modern Physics B*, **2002**, 16, 4423-4426	1.1	1
19	Formation of diluted III V nitride thin films by N ion implantation. *Journal of Applied Physics*, **2001**, 90, 2227-2234	2.5	37
18	Synthesis of InNxP1□ thin films by N ion implantation. *Applied Physics Letters*, **2001**, 78, 1077-1079	3.4	39
17	Thermal redistribution of photocarriers between bimodal quantum dots. *Journal of Applied Physics*, **2001**, 90, 1973-1976	2.5	60

16	Calculation of the ground state of shallow donors in GaAs1−xNx. *Journal of Applied Physics*, **2001**, 89, 789-791	2.5	5
15	Effect of band anticrossing on the optical transitions in GaAs1−xNx/GaAs multiple quantum wells. *Physical Review B*, **2001**, 64,	3.3	80
14	Nitrogen-induced enhancement of the free electron concentration in sulfur implanted GaNxAs1−x. *Applied Physics Letters*, **2000**, 77, 2858-2860	3.4	27
13	Increased electrical activation in the near-surface region of sulfur and nitrogen coimplanted GaAs. *Applied Physics Letters*, **2000**, 77, 3607-3609	3.4	12
12	Nitrogen-induced increase of the maximum electron concentration in group III-N-V alloys. *Physical Review B*, **2000**, 61, R13337-R13340	3.3	60
11	Structural and optical properties of self-assembled InAs/GaAs quantum dots covered by InxGa1−xAs (0?x?0.3). *Journal of Applied Physics*, **2000**, 88, 3392-3395	2.5	39
10	Nature of the fundamental band gap in GaNxP1−x alloys. *Applied Physics Letters*, **2000**, 76, 3251-3253	3.4	211
9	A mechanistic study of the antibacterial effect of silver ions on Escherichia coli and Staphylococcus aureus **2000**, 52, 662		1
8	A mechanistic study of the antibacterial effect of silver ions on Escherichia coli and Staphylococcus aureus **2000**, 52, 662		16
7	Alignment of misfit dislocations in the In0.52Al0.48As/InxGa1−xAs/In0.52Al0.48As/InP heterostructure. *Applied Physics Letters*, **1998**, 72, 311-313	3.4	0
6	Observation of post-deposition resistance relaxation during growth of semicontinuous metal films. *Thin Solid Films*, **1997**, 295, 315-319	2.2	4
5	Surface interaction and resistance relaxation of thin metal films on mica and fullerene substrates. *Solid State Communications*, **1996**, 99, 241-246	1.6	1
4	Performance of Beamline 4W1C for x-ray diffuse scattering station at Beijing Synchrotron Radiation Facility. *Review of Scientific Instruments*, **1995**, 66, 1694-1695	1.7	6
3	Characterization of Growth Defects in ZnTe Single Crystals. *Materials Research Society Symposia Proceedings*, **1994**, 299, 203		1
2	Characterization of Growth Defects in ZnTe Single Crystals. *Materials Research Society Symposia Proceedings*, **1993**, 302, 451		
1	Determination of 3-Dimensional Defect Structures in Gallium Arsenide Epilayers on Silicon Using White Beam Synchrotron Radiation Topography in both Transmission and Grazing Bragg-Laue Geometry. *Materials Research Society Symposia Proceedings*, **1989**, 160, 469		3